

FRED

Ultrafast Soft Recovery Diode, 20A/400V

Description

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery character of the diodes offers buffer in most applications. These devices are suited for power converters and other applications where the switching losses are not significant portion of the total losses.

Features

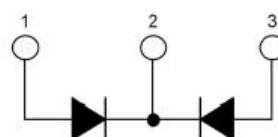
- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low IR value
- High surge capacity
- Epitaxial chip construction

Product Summary	
VR	400 V
IF(AV)	2*10A
trr	22 ns



Application

- Snubber diode
- Switched mode power supply
- Uninterruptible power supplies (UPS)



Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	V _{RRM}		400	V
Continuous forward current	I _{F(AV)}	T _C = 110°C	20	A
Single pulse forward current	I _{FSM}	T _C = 25°C	150	
Maximum repetitive forward current	I _{FRM}	Square wave, 20kHz	50	
Operating junction	T _j		175	°C
Storage temperatures	T _{stg}		-55 to +175	°C

Electrical characteristics (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min	Typ.	Max.	Units
Breakdown voltage Blocking voltage	V _{BR} , V _R	I _R =100μA	400			V
Forward voltage (Per Diode)	V _F	I _F =10 A		1.20	1.40	
		I _F =10 A, T _j =125°C		1.10	1.35	
Reverse leakage current(Per Diode)	I _R	V _R = 400V			10	μA
		T _j =150°C, V _R =400V			100	
Reverse recovery time(Per Diode)	t _{rr}	I _F =0.5A, I _R =1A, I _{RR} =0.25A			35	ns
		I _F =1A, V _R =30V, di/dt =200A/us		22	30	

Thermal characteristics

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	4.0	°C/W

Typical Characteristics

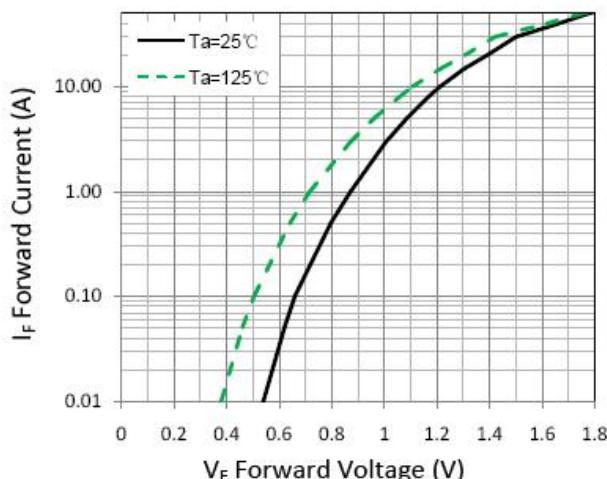


Figure 1. Forward Characteristic(typ.)

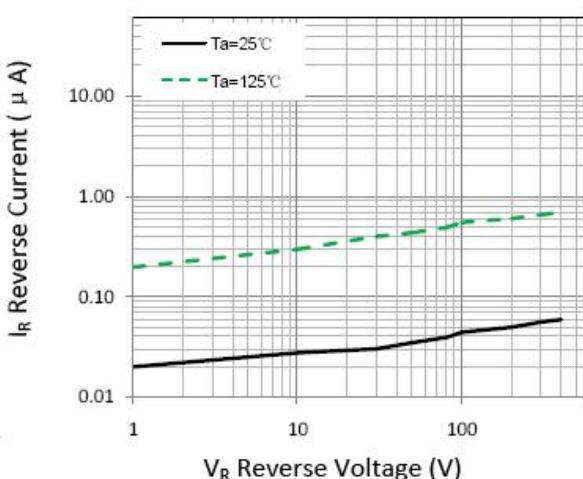


Figure 2. Reverse Characteristic (typ.)